



High-reliability discrete products  
and engineering services since 1977

# MJ802(NPN), MJ4502(PNP)

COMPLEMENTARY SILICON HIGH POWER  
TRANSISTORS

## FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

## MAXIMUM RATINGS

Rating	Symbol	Value	Units
Collector-emitter voltage ( $I_B = 0$ )	$V_{CEO}$	90	V
Collector-base voltage ( $I_E = 0$ )	$V_{CBO}$	100	V
Emitter base voltage ( $I_C = 0$ )	$V_{EBO}$	4	V
Collector current	$I_C$	30	A
Base current	$I_B$	7.5	A
Total power dissipation $T_C \leq 25^\circ\text{C}$	$P_{tot}$	200	W
Storage temperature range	$T_{stg}$	-65 to +200	°C
Maximum operating junction temperature	$T_J$	200	°C
Thermal resistance, junction to case	$R_{thj-c}$	0.875	°C/W

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-emitter sustaining voltage <sup>(1)</sup> ( $I_B = 0$ , $I_C = 200\text{mA}$ )	$V_{CEO(sus)}$	90	-	-	V
Collector cutoff current ( $I_E = 0$ , $V_{CB} = 100\text{V}$ ) ( $I_E = 0$ , $V_{CB} = 100\text{V}$ , $T_C = 150^\circ\text{C}$ )	$I_{CBO}$	-	-	1	mA
Emitter cutoff current ( $I_C = 0$ , $V_{EB} = 4\text{V}$ )	$I_{EBO}$	-	-	1	mA
Collector emitter sustaining voltage <sup>(1)</sup> ( $R_{BE} = 100\Omega$ , $I_C = 200\text{mA}$ )	$V_{CE(sus)}$	100	-	-	V
DC current gain <sup>(1)</sup> ( $I_C = 7.5\text{A}$ , $V_{CE} = 2\text{V}$ )	$h_{FE}$	25	-	100	V
Collector emitter saturation voltage <sup>(1)</sup> $I_C = 7.5\text{A}$ , $I_B = 0.75\text{A}$	$V_{CE(sat)}$	-	-	0.8	V
Base emitter saturation voltage <sup>(1)</sup> $I_C = 7.5\text{A}$ , $I_B = 0.75\text{A}$	$V_{BE(sat)}$	-	-	1.3	V
Base emitter voltage <sup>(1)</sup> $I_C = 7.5\text{A}$ , $V_{CE} = 2\text{V}$	$V_{BE}$	-	-	1.3	V
Transition frequency $I_C = 1\text{A}$ , $V_{CE} = 10\text{V}$ , $f = 1\text{MHz}$	$f_T$	2	-	-	MHz

Note 1: Pulse duration = 300μs, duty cycle 1.5%.



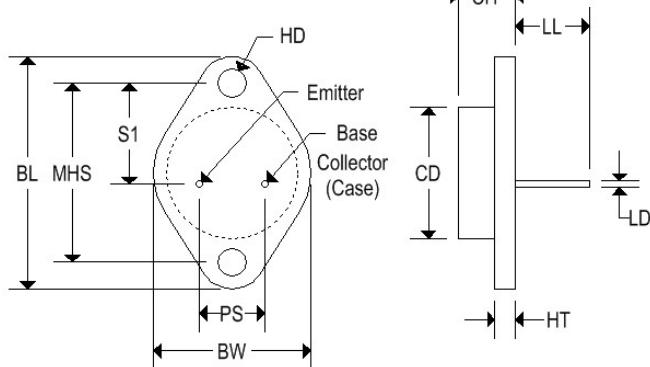
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## MECHANICAL CHARACTERISTICS

<b>Case</b>	TO-3
<b>Marking</b>	Alpha-numeric
<b>Pin out</b>	See below



	TO-3			
	Inches		Millimeters	
	Min	Max	Min	Max
CD	-	0.875	-	22.220
CH	0.250	0.380	6.860	9.650
HT	0.060	0.135	1.520	3.430
BW	-	1.050	-	26.670
HD	0.131	0.188	3.330	4.780
LD	0.038	0.043	0.970	1.090
LL	0.312	0.500	7.920	12.700
BL	1.550 REF		39.370 REF	
MHS	1.177	1.197	29.900	30.400
PS	0.420	0.440	10.670	11.180
S1	0.655	0.675	16.640	17.150